Winbond Electronics Corp.

128K × 8 CMOS STATIC RAM

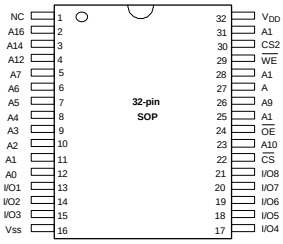
GENERAL DESCRIPTION

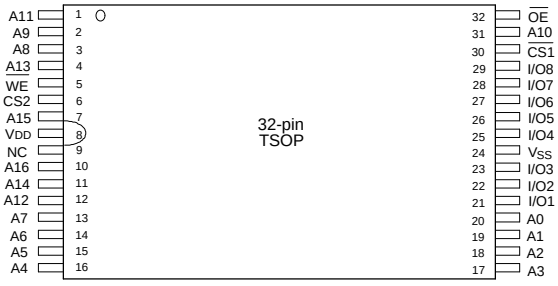
The W24L01 is a normal-speed, very low-power CMOS static RAM organized as 131072 × 8 bits that operates on a wide voltage range from 2.3V to 3.3V power supply. The W24L01 family, W24L01-LE and W24L01-LI, can meet the requirement of various operating temperature. This device is manufactured using Winbond's high performance CMOS technology.

FEATURES

- Low power consumption:
  - Active: 132 mW (max.)
  - Standby: 13.5 µW (max.) /2.5V ±0.2V
    16.5 µW (max.) /3.0V ±0.3V
- Access time: 70 nS /100 nS (max.)
- 2.3V to 3.3V supply voltage
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three-state outputs
- Battery back-up operation capability
- Data retention voltage: 1.5V (min.)
- Packaged in 32-pin 450 mil SOP, standard type one TSOP (8 mm × 20 mm), small type one TSOP (8 mm × 13.4 mm) and 48-pin CSP

PIN CONFIGURATIONS

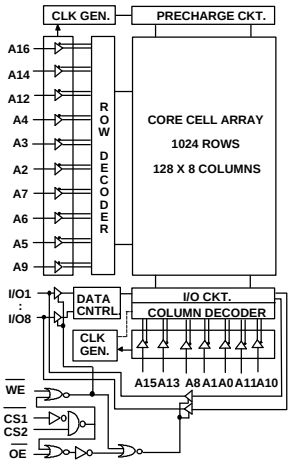




48-pin CSP TOP VIEW

	1	2	3	4	5	6
A	A0	A1	CS2	A3	A6	A8
B	I/O5	A2	$\overline{WE}$	A4	A7	I/O1
C	I/O6		NC	A5		I/O2
D	VSS					VCC
E	VCC					VSS
F	I/O7		NC	NC		I/O3
G	I/O8	$\overline{OE}$	$\overline{CS1}$	A16	A15	I/O4
H	A9	A10	A11	A12	A13	A14

BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0–A16	Address Inputs
I/O1–I/O8	Data Inputs/Outputs
$\overline{CS1}$, CS2	Chip Select Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
VDD	Power Supply
VSS	Ground
NC	No Connection

TRUTH TABLE

$\overline{CS1}$	CS2	$\overline{OE}$	$\overline{WE}$	MODE	I/O1- I/O8	V_{DD} CURRENT
H	X	X	X	Not Selected	High Z	I_{SB}, I_{SB1}
X	L	X	X	Not Selected	High Z	I_{SB}, I_{SB1}
L	H	H	H	Output Disable	High Z	I_{DD}
L	H	L	H	Read	Data Out	I_{DD}
L	H	X	L	Write	Data In	I_{DD}

DC CHARACTERISTICS

Absolute Maximum Ratings

PARAMETER		RATING	UNIT
Supply Voltage to V_{SS} Potential		-0.5 to +4.6	V
Input/Output to V_{SS} Potential		-0.5 to V_{DD} +0.5	V
Allowable Power Dissipation		1.0	W
Storage Temperature		-65 to +150	°C
Operating Temperature	LE	-20 to 85	°C
	LI	-40 to 85	°C

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

Operating Characteristics

(V_{DD} = 3.0V ±0.3V; V_{DD} = 2.5V ±0.2V, V_{SS} = 0V; T_A (°C) = -20 to 85 for LE, -40 to 85 for LI)

PARAMETER	SYM.	TEST CONDITIONS	3.0V			2.5V			UNIT
			MIN.	TYP.*	MAX.	MIN.	TYP.*	MAX.	
Input Low Voltage	V_{IL}	-	-0.2	-	+0.4	-0.2	-	+0.4	V
Input High Voltage	V_{IH}	-	+2.2	-	V_{DD} +0.3	+2.0	-	V_{DD} +0.2	V
Input Leakage Current	I_{LI}	V_{IN} = V_{SS} to V_{DD}	-1	-	+1	-1	-	+1	µA
Output Leakage Current	I_{LO}	$V_{I/O}$ = V_{SS} to V_{DD}, $\overline{CS1}$ = V_{IH} (min.) or CS2 = V_{IL} (max.) or $\overline{OE}$ = V_{IH} (min.) or $\overline{WE}$ = V_{IL} (max.)	-1	-	+1	-1	-	+1	µA
Output Low Voltage	V_{OL}	I_{OL} = +2.1 mA, V_{DD} = 3.0V I_{OL} = +0.5 mA, V_{DD} = 2.5V	-	-	0.4	-	-	0.4	V
Output Low Voltage	V_{OH}	I_{OH} = -1.0 mA, V_{DD} = 3.0V I_{OH} = -0.5 mA, V_{DD} = 2.5V	2.2	-	-	2.0	-	-	V

Operating Characteristics, continued

PARAMETER	SYM.	TEST CONDITIONS	3.0V			2.5V			UNIT
			MIN.	TYP.*	MAX.	MIN.	TYP.*	MAX.	
Operating Power Supply Current	I_{DD}	$\overline{CS1}$ = V_{IL} (max.) and CS2 = V_{IH} (min.) , I/O = 0 mA, Cycle = min. Duty = 100%	-	-	45	-	-	25	mA
Standby Power Supply Current	I_{SB}	$\overline{CS1}$ = V_{IH} (min.) or CS2 = V_{IL} (max.), Cycle = min. Duty = 100%	-	-	0.3	-	-	0.3	mA
	I_{SB1}	$\overline{CS1}$ ≥ V_{DD} -0.2V or CS2 ≤ 0.2V	-	0.5	5	-	0.5	5	µA

Note: Typical parameter is measured under ambient temperature T_A = 25° C and V_{DD} = 3.0V /2.5V

CAPACITANCE

(T_A = 25° C, f = 1 MHz)

PARAMETER	SYM.	CONDITIONS	MAX.	UNIT
Input Capacitance	C_{IN}	V_{IN} = 0V	8	pF
Input/Output Capacitance	$C_{I/O}$	V_{OUT} = 0V	10	pF

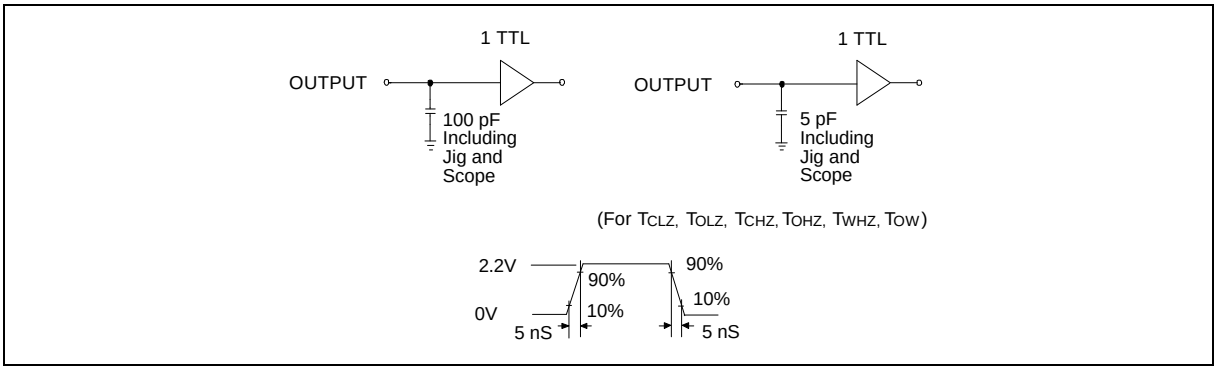
Note: These parameters are sampled but not 100% tested.

AC CHARACTERISTICS

AC Test Conditions

PARAMETER	CONDITIONS
Input Pulse Levels	0V to 2.2V
Input Rise and Fall Times	5 nS
Input and Output Timing Reference Level	1.5V, V_{DD} = 3.0V
	1.1V, V_{DD} = 2.5V
Output Load	See the drawing below

AC Test Loads and Waveform



AC Characteristics, continued

(V_{DD} = 3.0V ±0.3V; V_{DD} = 2.5V ±0.2V; V_{SS} = 0V; T_A (°C) = -20 to 85 for LE, -40 to 85 for LI)

Read Cycle

PARAMETER	SYM.	3.0V		2.5V		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	T_{RC}	70	-	100	-	nS
Address Access Time	T_{AA}	-	70	-	100	nS
Chip Select Access Time	T_{ACS}	-	70	-	100	nS
Output Enable to Output Valid	T_{AOE}	-	35	-	50	nS
Chip Selection to Output in Low Z	T_{CLZ}*	10	-	15	-	nS
Output Enable to Output in Low Z	T_{OLZ}*	5	-	5	-	nS
Chip Deselection to Output in High Z	T_{CHZ}*	-	30	-	35	nS
Output Disable to Output in High Z	T_{OHZ}*	-	30	-	35	nS
Output Hold from Address Change	T_{OH}	10	-	15	-	nS

* These parameters are sampled but not 100% tested

Write Cycle

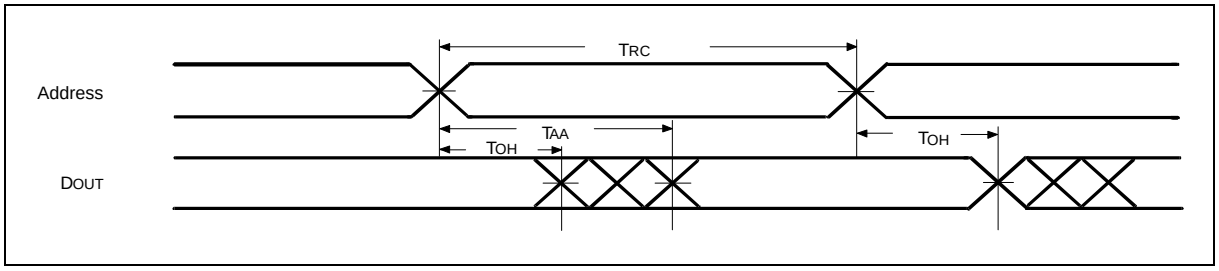
PARAMETER	SYM.	3.0V		2.5V		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	T_{WC}	70	-	100	-	nS
Chip Selection to End of Write	T_{CW}	60	-	70	-	nS
Address Valid to End of Write	T_{AW}	60	-	70	-	nS
Address Setup Time	T_{AS}	0	-	0	-	nS
Write Pulse Width	T_{WP}	55	-	70	-	nS
Write Recovery Time ($\overline{CS1}$, CS2, $\overline{WE}$)	T_{WR}	0	-	0	-	nS
Data Valid to End of Write	T_{DW}	30	-	50	-	nS
Data Hold from End of Write	T_{DH}	0	-	0	-	nS
Write to Output in High Z	T_{WHZ}*	-	25	-	35	nS
Output Disable to Output in High Z	T_{OHZ}*	-	25	-	35	nS
Output Active from End of Write	T_{OW}	5	-	10	-	nS

* These parameters are sampled but not 100% tested

TIMING WAVEFORMS

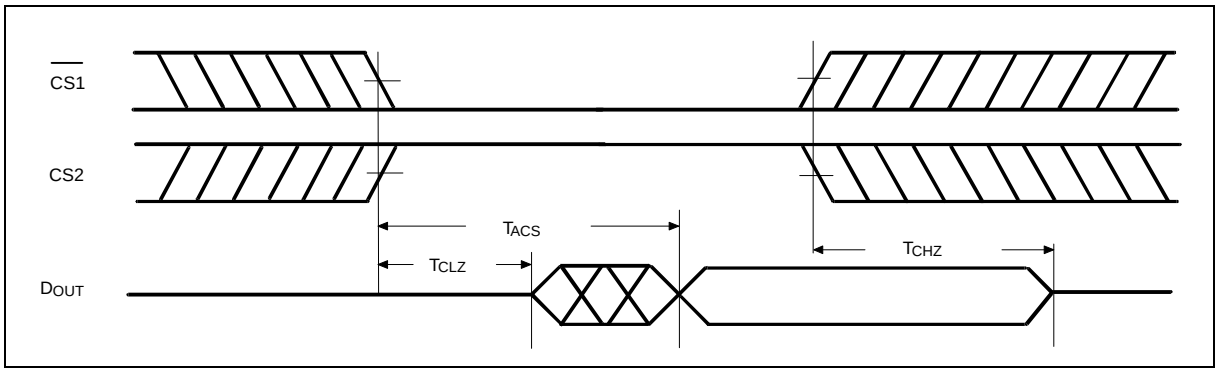
Read Cycle 1

(Address Controlled)



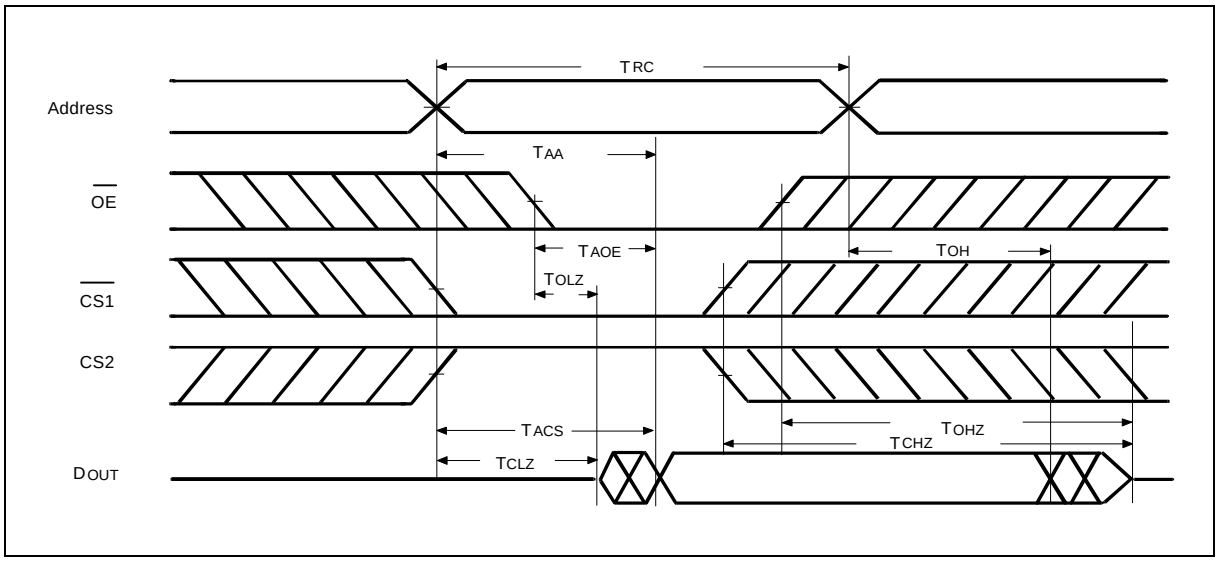
Read Cycle 2

(Chip Select Controlled)



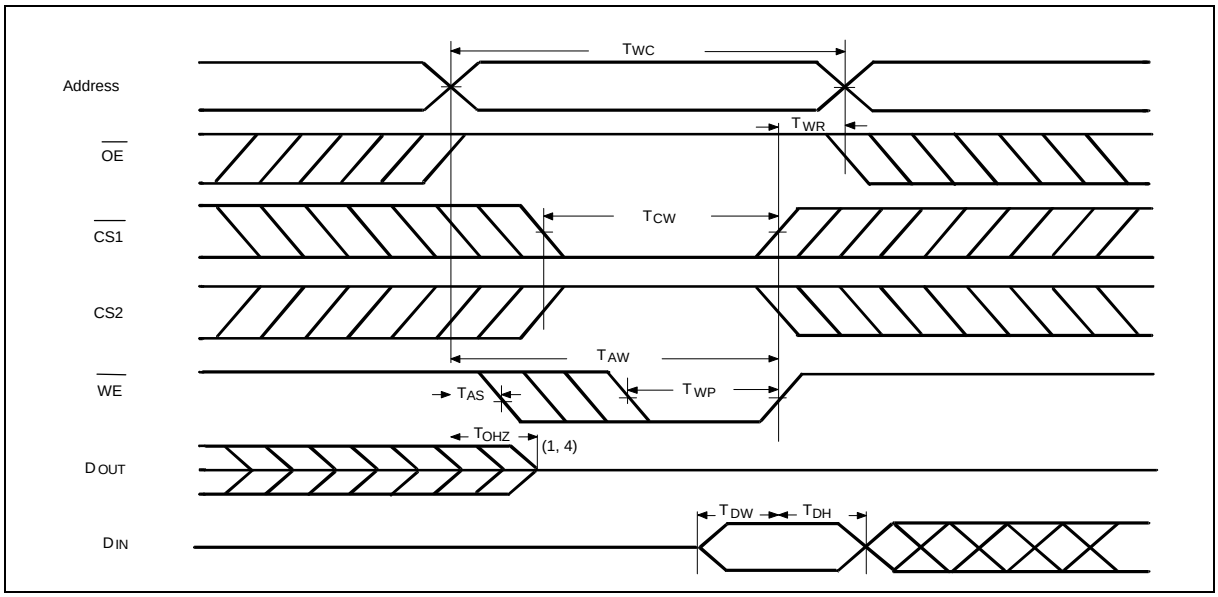
Read Cycle 3

(Output Enable Controlled)



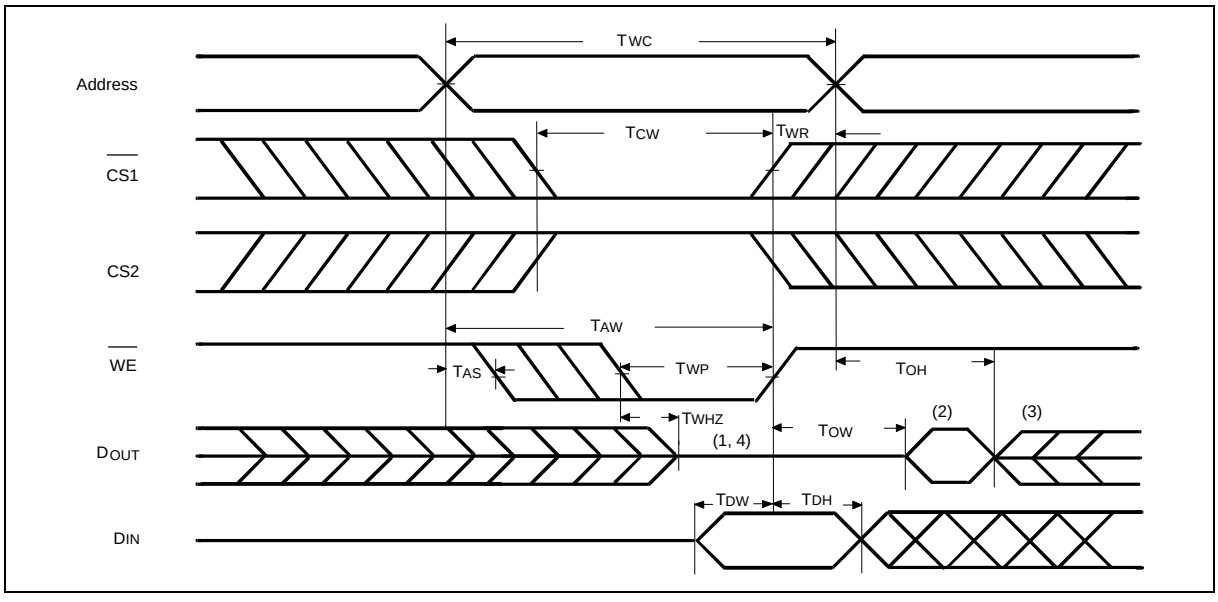
Timing Waveforms, continued

Write Cycle 1



Write Cycle 2

($\overline{OE}$ = VIL Fixed)



Notes:

1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
2. The data output from DOUT are the same as the data written to DIN during the write cycle.
3. DOUT provides the read data for the next address.
4. Transition is measured ±500 mV from steady state with CL = 5 pF. This parameter is guaranteed but not 100% tested.

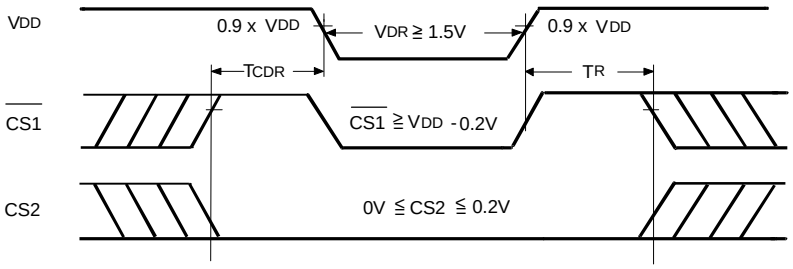
DATA RETENTION CHARACTERISTICS

(T_A (°C) = -20 to 85 for LE; -40 to 85 for LI)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DD} for Data Retention	V_{DR}	$\overline{CS1} \geq V_{DD}$ -0.2V or CS2 ≤ 0.2V	1.5	-	-	V
Data Retention Current	I_{DDDR}	$\overline{CS1} \geq V_{DD}$ -0.2V or CS2 ≤ 0.2V, V_{DD} = 3V	-	-	5	µA
Chip Deselect to Data Retention Time	T_{CDR}	See data retention waveform	0	-	-	nS
Operation Recovery Time	T_R		T_{RC}*	-	-	nS

* Read Cycle Time

DATA RETENTION WAVEFORM



ORDERING INFORMATION

PART NO.	ACCESS TIME (nS)	OPERATING VOLTAGE (V)	OPERATING TEMPERATURE (°C)	PACKAGE
W24L01B-70LE	100/70	2.5V/3V	-20 to 85	CSP
W24L01Q-70LE	100/70	2.5V/3V	-20 to 85	Small type one TSOP
W24L01S-70LE	100/70	2.5V/3V	-20 to 85	450 mil SOP
W24L01T-70LE	100/70	2.5V/3V	-20 to 85	Standard type one TSOP
W24L01B-70LI	100/70	2.5V/3V	-40 to 85	CSP
W24L01Q-70LI	100/70	2.5V/3V	-40 to 85	Small type one TSOP
W24L01S-70LI	100/70	2.5V/3V	-40 to 85	450 mil SOP
W24L01T-70LI	100/70	2.5V/3V	-40 to 85	Standard type one TSOP

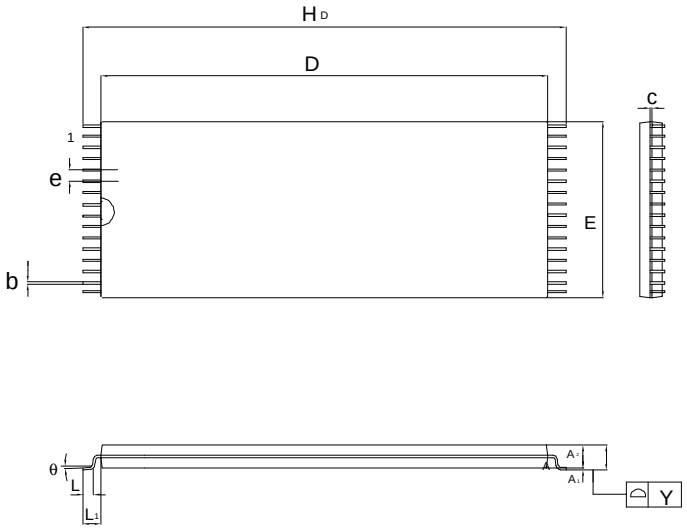
Notes:

1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

Winbond Electronics Corp.

PACKAGE DIMENSIONS

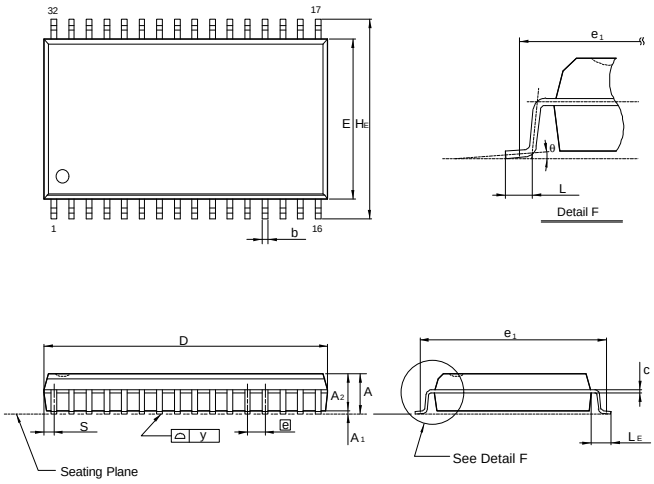
32-pin Small Type One TSOP



Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.049	—	—	1.25
A_1	0.002	—	0.006	0.05	—	0.15
A_2	0.037	0.039	0.041	0.95	1.00	1.05
b	0.007	0.008	0.009	0.17	0.20	0.27
c	0.0056	0.0059	0.0062	0.14	0.15	0.16
D	0.461	0.465	0.469	11.70	11.80	11.90
E	0.311	0.315	0.319	7.90	8.00	8.10
H_D	0.520	0.528	0.536	13.20	13.40	13.60
e	—	0.020	—	—	0.50	—
L	0.012	0.020	0.028	0.30	0.50	0.70
L_1	0.027	—	—	0.675	—	—
Y	0.000	—	0.004	0.00	—	0.10
θ	0	3	5	0	3	5

Controlling dimension: Millimeters

32-pin SOP Wide Body

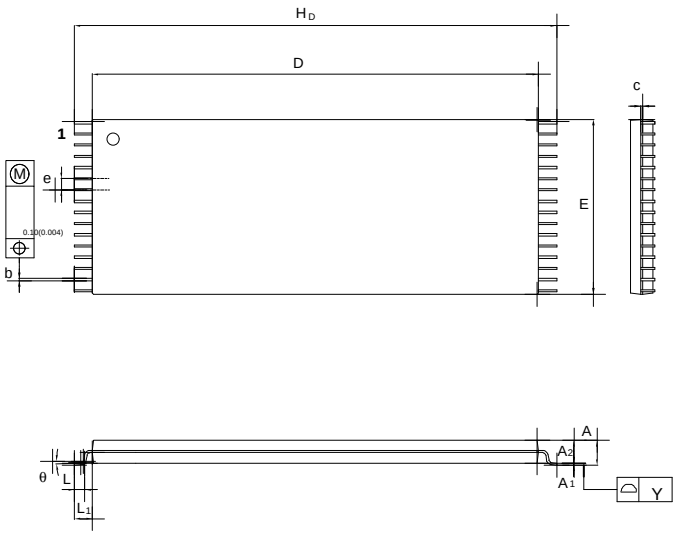


Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.118	—	—	3.00
A_1	0.004	—	—	0.10	—	—
A_2	0.101	0.106	0.111	2.57	2.69	2.82
b	0.014	0.016	0.020	0.36	0.41	0.51
c	0.006	0.008	0.012	0.15	0.20	0.31
D	—	0.805	0.817	—	20.45	20.75
E	0.440	0.445	0.450	11.18	11.30	11.43
e	0.044	0.050	0.056	1.12	1.27	1.42
H_E	0.546	0.556	0.556	13.87	14.12	14.38
L	0.023	0.031	0.039	0.58	0.79	0.99
L_E	0.047	0.055	0.063	1.19	1.40	1.60
S	—	—	0.036	—	—	0.91
y	—	—	0.004	—	—	0.10
θ	0°	—	10°	0°	—	10°

Notes:
1. Dimensions D Max. & S include mold flash or tie bar burrs.
2. Dimension b does not include dambar protrusion/intrusion.
3. Dimensions D & E include mold mismatch and determined at the mold parting line.
4. Controlling dimension: Inches
5. General appearance spec should be based on final visual inspection spec.

Package Dimensions, continued

32-pin Standard Type One TSOP



Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.047	—	—	1.20
A_1	0.002	—	0.006	0.05	—	0.15
A_2	0.037	0.039	0.041	0.95	1.00	1.05
b	0.007	0.008	0.009	0.17	0.20	0.23
c	0.005	0.006	0.007	0.12	0.15	0.17
D	0.720	0.724	0.728	18.30	18.40	18.50
E	0.311	0.315	0.319	7.90	8.00	8.10
H_D	0.780	0.787	0.795	19.80	20.00	20.20
e	—	0.020	—	—	0.50	—
L	0.016	0.020	0.024	0.40	0.50	0.60
L_1	—	0.031	—	—	0.80	—
Y	0.000	—	0.004	0.00	—	0.10
θ	1	3	5	1	3	5

Controlling dimension: Millimeters

VERSION HISTORY

VERSION	DATE	PAGE	DESCRIPTION
A1	Feb. 1998		Initial Issued
A2	Apr. 1998	3	Add standby power supply current (I_{SB1}) typical parameter when operation temperature T_A = 25° C
A3	June 1998	1	Change supply voltage range: from (2.7V to 3.6V) to (2.3V to 3.3V) Modify power consumption: - Active : 132 mW (max.) - Standby: 13.5 µW (max.) /2.5V ±0.2 16.5 µW (max.) /3.0V ±0.3
		2, 3	Correct Operating Characteristics: V_{IL} from (-0.5V to +0.6V) to (-0.2V to +0.4V) V_{IH} (max.) from V_{DD} +0.5V to V_{DD} +0.3V for 3.0V from V_{DD} +0.5V to V_{DD} +0.2V for 2.5V I_{DD} (max.) from 20 mA to 45 mA for 3.0V from 20 mA to 25 mA for 2.5V I_{SB} (max.) from 1 mA to 0.3 mA Modify V_{OL}, V_{OH} test conditions
		3	Correct Capacitance: C_{IN} (max.) from 6 pF to 8 pF $C_{I/O}$ (max.) from 8 pF to 10 pF Correct AC Characteristics and AC Test Waveform Input Pulse Levels from (0V to 2.4V) to (0V to 2.2V) Input and Output Timing Reference Level from 1.2V to 1.5V for 3.0V form 1.2V to 1.1V for 2.5V
		4	T_{WHZ}*, T_{OHZ}* from 30 nS to 35 nS T_{CW} from 50 nS to 60 nS for 3V T_{AW} from 50 nS to 60 nS for 3V T_{WP} from 50 nS to 55 nS for 3V
		7	Correct V_{DR} (min.) from 2.0V to 1.5V
		8	Modify Ordering Information: access time (nS) operating voltage(V) -70 2.7V to 3.0V -100 2.3V to 2.7V W24L01-LI operating temperature(°C) from -20–85 to -40–85
A4	Oct. 1998	1, 8, 9	Add SOP package type
A5	Jan. 1999	1	Add SOP package pin configuration

Winbond Electronics Corp.

Headquarters
No. 4, Creation Rd. III,
Science-Based Industrial Park,
Hsinchu, Taiwan
TEL: 886-3-5770066
FAX: 886-3-5796096
http://www.winbond.com.tw/
Voice & Fax-on-demand: 886-2-27197006

Taipei Office
11F, No. 115, Sec. 3, Min-Sheng East Rd.,
Taipei, Taiwan
TEL: 886-2-27190505
FAX: 886-2-27197502

Winbond Electronics (H.K.) Ltd.
Rm. 803, World Trade Square, Tower II,
123 Hoi Bun Rd., Kwun Tong,
Kowloon, Hong Kong
TEL: 852-27513100
FAX: 852-27552064

Winbond Electronics North America Corp.
Winbond Memory Lab.
Winbond Microelectronics Corp.
Winbond Systems Lab.
2727 N. First Street, San Jose,
CA 95134, U.S.A.
TEL: 408-9436666
FAX: 408-5441798